Sim ulations of H elix U nw inding in Ferroelectric Liquid C rystals

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In bulk ferroelectric liquid crystals, the molecular director twists in a helix. In narrow cells, this helix can be unwound by an applied electric eld or by boundary elects. To describe helix unwinding as a function of both electric eld and boundary elects, we develop a mesoscale simulation model based on a continuum free energy discretized on a two-dimensional lattice. In these simulations, we determ ine both the director prole across the cell and the net electrostatic polarization. By varying the cell size, we show how boundary elects shift the critical eld for helix unwinding and lower the saturation polarization. O ur results are consistent with experimental data.

I. INTRODUCTION

One of the most extensively studied phases of liquid crystals, both for basic research and for applications, is the sm ectic-C * (Sm C *) phase of chiralm olecules. In this phase, the molecules lie in layers and are tilted with respect to the layer norm al direction. The combination of molecular chirality, smectic layering, and tilt order leads to two e ects: a ferroelectric polarization within the smectic layer plane and a helical modulation in the orientation of the molecular tilt from layer to layer [1]. The ferroelectric polarization is useful for display devices, which use an applied electric eld to switch the molecular orientation [2]. It is also useful for therm alsonsors, which m easure the tem perature variation of the polarization, known as the pyroelectric e ect [3, 4]. Both of these applications require a uniform orientation of the molecules. Hence, the helix must be suppressed, or unwound, by an applied electric eld or by boundary e ects.

Helix unw inding has been modeled through continuum elastic theory. In a bulk Sm C * phase, unw inding induced by an applied electric eld can be described by the sine-G ordon equation, presented below [5, 6, 7]. Under an electric eld, the helix distorts and the helical pitch increases. If the eld is increased above a critical threshold, the pitch diverges and the helix is suppressed. By contrast, helix unwinding induced by boundary e ects in a narrow cell is more com plex [8, 9, 10, 11]. In this case, a helix m ust have a series of disclination lines near the cell surfaces, which separate a twisted interior region from a uniform surface region. Continuum elastic theory shows that the unwinding transition is controlled by an energetic com petition between the helical state with disclinations and the uniform untwisted state. If the cell thickness is below a critical threshold com parable to the helical pitch, the uniform state is favored and the helix is suppressed. (A third possible mechanism for helix unwinding is shear ow [12], but this is not often used in Sm C * liquid crystals, and we will not discuss it here.)

In this paper, we investigate the unwinding of a Sm C * helix by boundary e ects, or by combined boundary and electric-eld e ects, through a series of M onte C arlo simulations of a continuum free energy discretized on a 2D lattice. These simulations serve two purposes. First, they allow us to visualize the complex director con guration within a narrow cell as a function of cell thickness and electric eld. W e obtain snapshots of the m olecular tilt prole through the helix unwinding process. Second, they allow us to relate the microscopic director con guration to two macroscopic variables, an average chiral order parameter and the net electrostatic polarization of the cell. The latter variable can be compared with experimental measurements of Sm C * cells.

In these simulations, we rst consider boundary e ects alone. W e simulate the Sm C * phase in narrow cells, and determ ine the structure of the helix as a function of cell. thickness. We con m that the helix unwinds at a threshold thickness approxim ately equal to the helical pitch, in agreem ent with continuum elastic theory. We then use the same M onte C arb approach to simulate helix unwinding due to the combined e ects of cell boundaries and electric eld. In these simulations, we calculate both the molecular tilt pro le across the cell and the net electrostatic polarization. W e observe three distinct regimes of response, in which the helical pitch is rst distorted and then expelled as the applied eld is increased. By varying the cell thickness, we determ ine how boundary e ects shift the critical eld for helix unwinding and low er the saturation polarization. These simulation results are consistent with trends observed in experim ents.

The plan of this paper is as follows. In Sec. II, we review the continuum elastic theory of the Sm C * phase. We show how an applied electric eld unwinds the Sm C * helix in a bulk system, and sketch an approximate energetic argument for a nite cell. In Sec. III, we use

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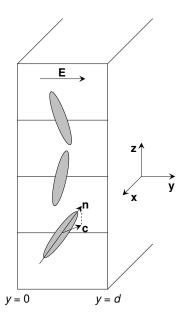


FIG.1: Idealized bookshelfgeom etry of a SmC * liquid crystal in a narrow cell. The helical axis is along the z-axis, perpendicular to the sm ectic layers. An electric eld is applied along the y-axis.

M onte C arlo simulations to investigate the e ects of nite cell thickness under zero applied electric eld. In Sec. IV, we combine the e ects of cell boundaries and applied electric eld to determ ine the tilt pro le and the polarization, and compare the polarization with experim entalm easurem ents.

II. THEORY

A Sm C * liquid crystal in a narrow cellhas the idealized bookshelf geom etry shown in Fig. 1. The molecules lie in layers, and they are tilted with respect to the sm ectic layer norm al. The 3D orientation is represented by the director n. This unit vector can be written in spherical coordinates as $n = (\sin \cos ; \sin \sin ; \cos)$, where

is the polar angle of the tilt and is the azim uthal angle. The molecular tilt is conventionally described in terms of the projection of n into the layer plane, $c = (\sin \cos s)$.

In this geom etry, we expect the director to depend on the y and z coordinates. The z coordinate is along the sm ectic layer norm al. Because of the molecular chirality, the molecular orientation rotates in a helix from layer to layer, which makes the director a periodic function of z. The y coordinate is the narrow dimension of the cell, with a thickness d of order microns, across which an electric

eld E is applied. The molecules may interact strongly with the front and back surfaces of the cell, at y = 0 and d. As a result, the director may rotate as a function of y. By contrast, we do not expect the director to depend on the third coordinate x. In this bookshelf geometry, the system is uniform as a function of x. (In certain

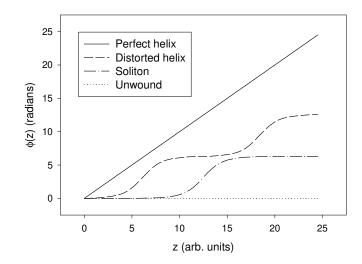


FIG.2: Unwinding of a SmC helix in a bulk system under an applied electric eld E. Solid line: Perfect helix for E = 0. D ashed line: D istorted helix under moderate E. D ot-dashed line: Single soliton in the director, near the threshold for helix unwinding. D otted line: U nwound uniform director.

liquid crystals, the smectic layers buckle as a function of x [13, 14, 15, 16], but we do not consider that e ect here.) For that reason, we write the angles and as functions of y and z.

W e can now construct the simplest model free energy to describe variations in the director. This model must include four interactions. First, the smectic layer order interacts with the molecular orientation, and favors a particular tilt of the molecules with respect to the layers. This interaction can be expanded as a power series in the tilt magnitude jcj = sin , which gives $\frac{1}{2}$ rjcj + $\frac{1}{4}$ ujcj , for some series coe cients r and u. In term s of these coe cients, the favored tilt is $jcj = (r=u)^{1=2}$. Second, there is an electroclinic interaction of the molecules with the applied electric eld E. Because of the molecular chirality, this interaction couples the eld in the y direction with the tilt in the x direction, so it can be $c = bE_{x}c_{x}$. In other words, the written as bz E electrostatic polarization is P = bz c, or $P_v = bc_x$. Third, there is a chiral interaction that favors a variation of the director from layer to layer, which can be writz c @c=@z. Fourth, there is the Frank free ten as energy for elastic distortions of the director, which lim its the variations from layer to layer. This contribution can be written as $\frac{1}{2}$ K ($(Q_i c_i)$) ($(Q_i c_i)$, sum med over i and j. Putting these pieces together, the total free energy density becom es

$$F = \frac{1}{2}r_{j}c_{j}^{2} + \frac{1}{4}u_{j}c_{j}^{4} + bz \quad E \quad c \quad z \quad \frac{@c}{@z} + \frac{1}{2}K \quad (@_{i}c_{j}) \quad (@_{i}c_{j}) :$$
(1)

This free energy is invariant under rotations in the xy plane, but it is not invariant under re ections, because re ection symmetry is broken by the molecular chirality.

W e can see in m ediately that this m in in alm odel leads to a helix in the z direction. Consider a director of the form c = (ccos ; csin), where the magnitude c = sin is constant and the azim uthal angle depends on position. The free energy density simpli es to

$$F = \frac{1}{2}rc^{2} + \frac{1}{4}uc^{4} \quad bE c\cos \qquad c^{2}\frac{\theta}{\theta z} + \frac{1}{2}Kc^{2}jc \quad j^{2}:$$
(2)

In the lim it of zero electric eld, E = 0, we m in in ize this free energy over to obtain

$$\frac{0}{0z} = \frac{1}{K} :$$
 (3)

Hence, the azim uthal angle increases linearly as $(z) = _0 + q_0 z$, with $q_0 = -K$, as shown by the solid line in Fig. 2. This linear increase in implies a perfect sinusoidal helix in c.

Thism inim alm odel also predicts unwinding of the helix under an applied electric eld. This behavior is analogous to the theory of M eyer for a cholesteric phase in an electric orm agnetic eld [5, 6, 7]. For $E \in 0, m$ in im izing the free energy over gives

$$\frac{\varrho^2}{\varrho z^2} = \frac{bE}{Kc} \sin \quad : \tag{4}$$

This is the standard sine-G ordon equation. The form of the solutions depends on the value of E, as shown in Fig.2. For low E, the helix is distorted, so that the director is approximately aligned with the eld in most of the system . As E increases, the helix becomes even more distorted, with sharper steps between domains where is approximately a multiple of 2. Eventually the system crosses over into regime of uniform domains separated by sharp domain walls, or solitons. In that regime, a single soliton has the probe (z) = 2 $4 \tan^1$ [exp(($z_{wall})=$)], where $= (2K \ c=bE \)^{=2}$. As E continues to increase, the spacing between the domain walls increases, or equivalently their density decreases. At the critical threshold $E = (\ ^2=8)(\ ^2c=bK)$, the last domain wallvanishes and the system becomes uniform .

The question is now: W hat other types of in uncess can also unwind a Sm C * helix? C learly one possibility is surface e ects. Interactions along the front and back surfaces of a nite cell, at y = 0 and d, can anchor the director at those surfaces. If the elastic interactions described by the parameter K are su ciently strong, and the cell thickness d is not too big, then this anchoring m ay extend throughout the interior of the cell, giving a uniform director. This is the basis of surface-stabilized ferroelectric liquid crystal cells [2].

The threshold thickness for unwinding a helix is not obvious. As shown in Fig. 1, the helical pitch is along the z direction, but the narrow dimension of the cell is along the y direction. Because these directions are perpendicular, there is no simple geometric reason why a helix must unwind when the cell thickness is less than the pitch. Rather, there must be some energetic argument that relates these two length scales.

A n energetic argum ent has been developed for narrow cells of the cholesteric phase [8, 9], and has been extended

to narrow cells of the Sm C * phase [10, 11]. In its sim plest form, the argument can be stated as follows [17]. If a cell has a helix in the interior, but a uniform director along the front and back surfaces, then it must have a series of disclination lines running along the x direction near the surfaces. There must be one disclination line for each helical pitch. We can compare the energy of the helix (with disclinations) with the energy of the uniform state to nd the threshold thickness for helix unwinding. The energy of the helix (with disclinations) is the negative energy gained from the helix plus the positive energy lost to the disclinations,

$$\frac{E}{\text{volume}} \qquad K q_0^2 + \frac{E_{\text{line}}}{(d) (p \text{itch})}; \qquad (5)$$

where E_{line} is the disclination line energy per unit length. The helix unwinds if E > 0, which im plies

$$d > \frac{E_{line}}{K}$$
 (pitch): (6)

Since the line energy $E_{\rm line}$ should be of order K , the threshold thickness should be comparable to the pitch.

In the following sections, we test this argument through a series of M onte C arb simulations. In these simulations, we obtain snapshots of the director conguration for dierent cell thicknesses, both at zero eld and under an applied electric eld. These snapshots provide speci cillustrations of the disclinations discussed above. For zero eld, the simulations con m that the helix unwinds at a critical thickness approximately equal to the helical pitch. For nite eld, the simulations show helix unwinding induced by the combined e ects of boundaries and electric eld in a cell above the critical thickness. In both cases, we relate the microscopic snapshots of the director conguration to macroscopic variables. One of these variables, the net electrostatic polarization, can be compared with experimental measurements.

III. FINITE CELLS UNDER ZERO ELECTRIC FIELD

To model helix unwinding in a nite cell of the SmC* phase, we map the system onto a 2D square lattice. The lattice dimensions represent the yz plane shown in Fig.1: y is the narrow dimension of the cell and z is the smectic layer normal. We assume the system is uniform in the x direction. On each lattice site (y;z) there is a 3D unit vector n (y;z) representing the local molecular director. This vector can be parametrized in terms of the polar angle (y;z) and azim uthalangle (y;z), or equivalently in terms of the projection c(y;z) into the smectic layer plane.

For the lattice simulations, we discretize the free energy of Eq. (1) to obtain

$$F = \frac{X}{(y;z)} \frac{1}{2} \operatorname{rig}(y;z) \, j + \frac{1}{4} \operatorname{uig}(y;z) \, j + bz \quad E \quad c(y;z)$$

$$z \frac{c(y;z) + c(y;z+1)}{2} [c(y;z+1) - c(y;z)]$$
(7)
+ $\frac{1}{2}K (\dot{p}(y+1;z) - c(y;z)\hat{f} + \dot{p}(y;z+1) - c(y;z)\hat{f});$

with E = 0 in this section. This free energy is similar to the free energy studied in Ref. [16] but with one important di erence: that paper simulated the xy plane, but we now simulate the yz plane.

A further consideration for the simulations is boundary conditions. Experimental cells may be symmetric, with the local director aligned along the same direction on both front and back con ning walls, or they may be asymmetric, with the director aligned along one wall and an open boundary on the other side. In our simulations we use an aligning boundary condition with the director

xed on the wall at y = 0 with a speci ed tilt angle. On the other wall at y = d we use the boundary condition (c(y;z))=(0,y)=0. This arrangement can represent an asymmetric cell, or one half of a symmetric cell, with the other half a mirror image of the st. Experimental cells are very large in the z direction so that the top and bottom boundaries should not a ect the physics of the interior. In the simulations, we use the boundary condition (c(y;z))=(0,z)=(0,z) for the top and bottom boundaries.

We simulate the system with the parameters r = 0.007596, u = 1, b = 1, E = 0, K = 1.5, and = 0.25 and 0.125. The small value of r corresponds to a tilt angle of approximately 5. We use the large z dimension of 160, and several values of the thickness d in the y direction. For each set of parameters and system size, we begin the simulations in a disordered state at a high M onte C arbotem perature, and then slow ly reduce the tem perature until the system settles into a single ground state and the

uctuations in c become negligible. This procedure can be regarded as a simulated-annealing m in imization of the lattice free energy of Eq. (8).

To visualize the simulation results, we draw the yz plane in Figs. 3 and 4. The director con guration is represented by short lines that show the projection of the 3D director into the yz plane. Hence, vertical lines indicate $c_y = 0$, and tilted lines indicate $c_y \in 0$. Because the lines representing the director are drawn close together, helical regions resemble twisted ribbons.

Figure 3 shows the simulation results for = 0.25 and K = 1.5. For these parameters, the favored wavevector $is q_0 = -K$ 0:17, and hence the unperturbed pitch is 38. For a thickness of 10, the system is uniform, 2 =q₀ with $c_v = 0$ everywhere except near the top and bottom surfaces. Those distortions are edge e ects within a fractional pitch of the free surfaces, which do not a ect the bulk behavior inside the cell. Hence, we see that the system of thickness 10 is unwound. By contrast, for a thickness of 12, the system shows a well-de ned helix, with a periodic modulation of c, throughout the cell, except very close to the aligning surface at y = 0. Thus, there is a clear helix winding/unwinding transition as a function of thickness. The transition occurs at a critical thickness between 10 and 12 for a cell with asymmetric

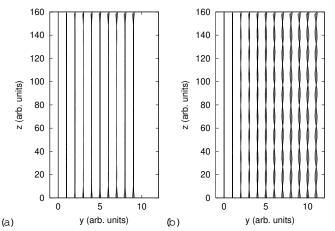


FIG.3:D irector con guration in the yz plane for simulations with = 0.25, leading to a pitch of approximately 38. The system has an aligning boundary along the left side (y = 0). Note that the y axis is exaggerated compared with the z axis. (a) For a thickness of 10 (y = 0 through 9), the system is uniform, except for some edge e ects at the top and bottom. (b) For a thickness of 12, the system has a clear helix.

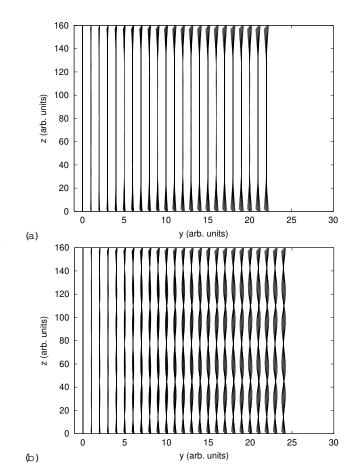


FIG. 4: Director con guration in the yz plane for simulations with = 0.125, leading to a pitch of approximately 75. (a) For a thickness of 23, the system is uniform, except for some edge e ects. (b) For a thickness of 25, there is a clear helix.

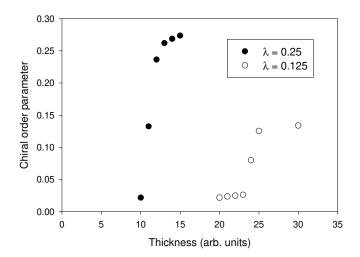


FIG. 5: The chiral order parameter de ned in Eq. (8), as a function of the system thickness d. For = 0.25 (pitch 38), the unwinding transition occurs at a thickness between 10 and 12. For = 0.125 (pitch 75), the transition occurs at a thickness between 23 and 25.

boundary conditions (or a half-thickness between 10 and 12 if the simulation is regarded as half of a symmetric cell). This critical thickness is not equal to the pitch, but it is certainly the same order of magnitude, in agreement with the theoretical expectation of Eq. (6).

Figure 4 shows the corresponding results for = 0.125. In this case, the favored wavevector is $q_0 = 0.083$, so the unperturbed pitch is $2 = q_0 = 75$. For a thickness of 23, the system is uniform, again except for some edge e ects near the top and bottom surfaces. By comparison, for a thickness of 25, there is a distinct helix throughout the interior of the cell. Thus, there is a helix winding/unwinding transition with a critical thickness between 23 and 25. This critical thickness is approximately twice the critical thickness of the previous case. Hence, we see that the critical thickness is approximately proportional to the pitch, again in agreement with the theoretical expectation.

For a quantizative m easurem ent of helix winding and unwinding, we must de ne a chiral order param eter. O ne sim ple choice of a chiral order param eter is just the chiral term of the free energy (8), without the factor of itself,

$$= \frac{1}{N_{\text{sites}}} \sum_{(y;z)}^{X} z \frac{c(y;z) + c(y;z+1)}{2}$$
[c(y;z+1) c(y;z)]: (8)

Figure 5 shows this order parameter as a function of the system thickness d for both series of simulations, with

= 0.25 and 0.125. For = 0.25, the plot shows a sharp transition between thickness 10 and 12, as jumps from 0.022 to 0.24. For = 0.125, there is a distinct transition between thickness 23 and 25, as jumps from 0.026 to 0.13. This analysis con m sthat the winding/unwinding

transition occurs at a thickness that is proportional to, and the same order of magnitude as, the helical pitch.

IV. FIN ITE CELLS UNDER AN ELECTRIC FIELD

In the previous section, we showed that a SmC * helix can be unwound by surface e ects in a nite cell. If the thickness is greater than the critical threshold, the helix is present at zero electric eld. However, when an electric eld is applied, the helix can be unwound by the combined e ects of the surfaces and the electric eld. In this section, we simulate that combination of surface and eld e ects.

For these simulations, we use the sam eM onte C arlo approach as in the previous section. We use the discretized free energy of Eq. (8) with the parameters r = 0.0625, u = 1, b = 1, K = 1.5, and= 0.25. This value of r corresponds to a tilt angle of approxim ately 15 . W e perform the simulations for four values of the cell thickness, d = 10, 20, 40, and 60, and scan through the electric eld E at each thickness. For these param eters, the unperturbed pitch is 2 K =38 and hence, based on the results of the previous section, the zero- eld winding/unw inding transition occurs at a thickness between 10 and 12. Hence, the simulations at thickness 10 should be unwound at all values of the electric eld, while the simulations at larger thickness should go through the winding/unwinding transition as a function of electric ed.

Figure 6 shows the simulation results for the system of thickness 20. For E = 0, the system has a helix everywhere in the cell, except a narrow region near the aligning boundary at y = 0. By comparison, for E = 0.004, the helix is suppressed in much of the cell. It persists only in regions of the cell near the free surfaces at the top and bottom. This behavior near the free surfaces is consistent with the previous section, which showed that free surfaces tend to favor the helicalm odulation. When the

eld increases to E = 0.006, the helix is suppressed in more of the cell, and it persists only in smaller regions near the top and bottom surfaces. Once the eld reaches E = 0.008, the helix is suppressed throughout the interior of the cell. The director in the cell is now uniform, except for very narrow edge e ects at the top and bottom. Hence, the electric eld has driven the nite cell through the helix winding/unwinding transition.

As in the previous section, we need an order parameter to describe the winding/unwinding transition quantitatively. In this case, the electrostatic polarization provides an experimentally relevant order parameter, which shows how the net polar order of the cell couples to the electric eld. As argued in Sec. II, the polarization is the quantity conjugate to the electric eld in the free energy, and hence P = bz c, or $P_y = bc_x$. We average this

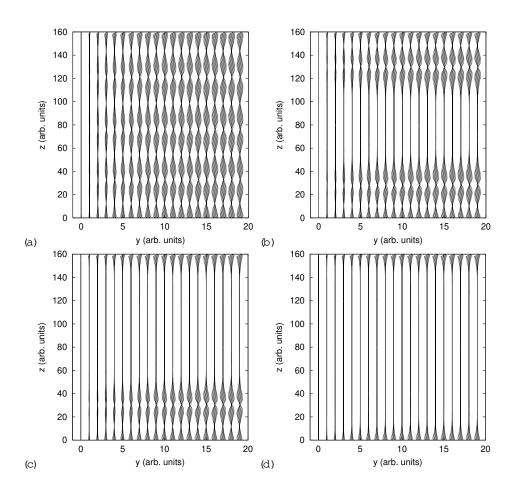


FIG.6: Director con guration in the yz plane as a function of increasing electric eld, for a xed thickness of 20. (a) E = 0. (b) E = 0.004. (c) E = 0.006. (d) E = 0.008.

quantity over the cell to obtain

$$P_{y} = \frac{1}{N_{sites}} X_{(y;z)} bc_{x} (y;z):$$
(9)

Figure 7 shows the simulation results for the polarization as a function of electric eld for each cell thickness. Figure 7(a) presents the results on a linear scale, and Fig. 7(b) presents the same results on a logarithm ic scale. Note that the polarization is not zero at zero eld because of the symmetry-breaking surface alignment at y = 0.

From the plots in Fig. 7, we can see that the system has three distinct regimes in its response to an electric eld. For low eld $E^{<}$ 0:01, there is a regime of helix unwinding. In this regime, an increasing electric eld gradually aligns the directors, suppresses the helix, and prevents the local polarization from averaging to zero. As a result, the net polarization increases rapidly as a function of eld. (This low - eld regime does not occur for the low est thickness d = 10, because the helix is suppressed by surface e ects even without a eld.) For intermediate eld 0:01[<] E [<] 1, there is a regime of suppressed twist. In this regime, the helix is already unwound, so the only e ect of electric eld is to increase the local tilt and polarization. Hence, the net polarization increases more slow ly, roughly as $E^{1=3}$. Finally, for high eld $E^{>}$ 1, there is a saturated regime. Here, the helix is already unwound, the local tilt is at its maximum value $c_x = 1$, and the polarization is at its maximum value of $P_y = b$. A lineagh the simulations only go to E = 12, we see that the polarization cannot increase at higher eld because it is already saturated.

In Fig. 7, we can also compare the relative polarization of thinner and thicker cells. For low eld, thinner cells have a higher polarization than thicker cells, because the helix reduces the polarization in thicker cells but the aligning boundary at y = 0 unwinds the helix in thinner cells. By contrast, for high eld, thicker cells have a higher polarization than thinner cells, because there is no helix at any thickness, and surface e ects at y = dsuppress the polarization in thinner cells. A sim ilar high-

eld lim it has been discussed by Shenoy et al. [18], who see the same e ect experim entally in cells with di erent boundary conditions. For interm ediate eld, the polarization of thinner and thicker cells must cross.

To compare our results with experimental measurements of the polarization as a function of electric eld, we must take into account one subtlety of the experiments. As shown by Ruth et al. [19, 20], the polarization

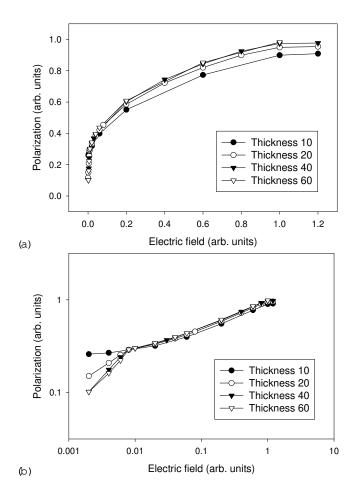


FIG. 7: Simulation results for the polarization as a function of electric eld in cells of four thicknesses. (a) Linear scale. (b) Logarithm ic scale. On the logarithm ic scale, note the three regimes of helix unwinding, suppressed twist, and saturation.

observed experimentally (by the triangle-wave technique or other techniques) is not the total polarization conjugate to the electric eld. Rather, it is a speci c nonlinear component of the polarization, which can be written as

$$P_{obs}(E) = P(E) E \frac{dP}{dE}$$
 : (10)

The di erence between the total polarization P (E) and the observable polarization P_{obs} (E) is smallwhen P (E) is saturated, but it is signi cantwhenever P (E) varies with E. Hence, we must extract P_{obs} (E) from the simulations and compare that quantity with experiments.

To extract $P_{obs}(E)$ from the simulations, we need to calculate the derivative dP = dE. For that reason, we t the simulation results for the polarization to the function P(E) = (1 + E) = (+ E). This is just an empirical

tting function, with no theoretical basis, but it gives a fairly good t to the data in Fig. 7 (a). We can then di erentiate this function and calculate the observable polarization $P_{obs}(E)$ that corresponds to the simulation results.

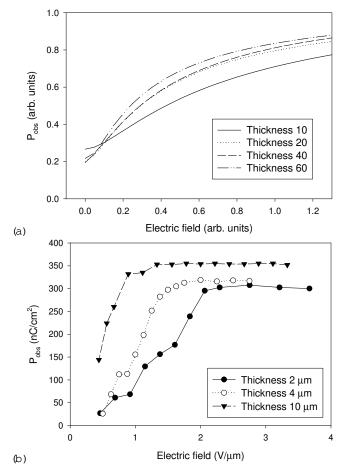


FIG.8: (a) Simulation results for the observable polarization $P_{obs} = P = E (dP = dE)$ in cells of four thicknesses. (b) Experimental data for P_{obs} in three cells [21].

Figure 8(a) shows the results for ${\tt P}_{\rm obs} \times {\tt E}$) extracted from the simulations at each system size. This function is sm all for low E , then increases towards its saturation level P_{obs} = b at high E . As discussed above, thinner cells have a higher value of P_{obs} at low eld, and thicker cells have a higher value of Pobs at high eld. By com parison, Fig. 8 (b) shows sam ple experim entalm easurem ents of Pobs as a function of applied electric eld in three cells with asymmetric boundary conditions [21]. The material is 10PPBN4 (described in Ref. [22]), and the tem perature is 7 C below the Sm A-Sm C transition. Note that the experimental data show the same general features as the theoretical plots. In particular, we see the same crossover between higher Pobs in thinner cells at low eld and higher Pobs in thicker cells at high eld. Thus, the simulation results are consistent with the trends seen in experim ents.

In conclusion, we have developed an approach for sim – ulating the helix winding/unwinding transition in Sm C * liquid crystals. This approach is based on a minimal model for the free energy, which includes a chiral term that favors a helicalm odulation of the director from layer to layer. This bulk free energy competes with surface effects and electric- eld e ects, which both favor a uniform alignment of the director. In zero eld, the competition between the bulk helix and the surface alignment leads to helix unwinding at a critical thickness approximately equal to the helical pitch. When an electric eld is applied, the eld-induced alignment adds to the surface effects, and induces helix unwinding even for thicker cells. The electrostatic polarization is an appropriate order param eterto quantify this eld-induced unwinding, and our simulation results for the polarization are consistent with experimental measurements.

- P.G. de Gennes and J. Prost, The Physics of Liquid Crystals, 2nd edition (Oxford, Oxford University Press, 1993).
- [2] J.W. Goodby, R.Blinc, N.A.Clark, S.T.Lagerwall, M. A.Osipov, S.A.Pikin, T.Sakurai, K.Yoshino, and B. Zeks, Ferroelectric Liquid Crystals: Principles, Properties and Applications (Gordon and Breach, Am sterdam, 1991).
- [3] J.W .O 'Sullivan, Yu.P.Panarin, and J.K.V ij J.Appl. Phys. 77, 1201 (1995).
- [4] K. Crandall, D. Shenoy, S. Gray, J. Naciri, and R. Shashidhar, Proc. IR IA -M SS on Infrared Materials, p. 173 (1999).
- [5] R.B.Meyer, Appl. Phys. Lett. 12, 281 (1968)
- [6] R.B.Meyer, Appl. Phys. Lett. 14, 208 (1969).
- [7] R.D.Kamien and J.V.Selinger, J.Phys.: Condens. M atter 13, R1 (2001).
- [B] P.E.C ladis and M.K lem an, M ol. Cryst. Liq. Cryst. 16, 1 (1972).
- [9] M.Luban, D.M. ukam el, and S.Shtrikm an, Phys. Rev. A 10, 360 (1974).
- [10] M. G logarova, L. Lejœk, J. Pavel, V. Janovec, and J. Fousæk, M ol. Cryst. Liq. Cryst. 91, 309 (1983).
- [11] T. Povse, I. Musevic, B. Zeks, and R. Blinc, Liq. Cryst.

A cknow ledgm ents

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14,1587 (1993).

- [12] A.D.Rey, Phys.Rev.E 53, 4198 (1996).
- [13] G. P. Craw ford, R. E. Geer, J. Naciri, R. Shashidhar, and B. R. Ratna, Appl. Phys. Lett. 65, 2937 (1994).
- [14] R.E.Geer, S.J.Singer, J.V.Selinger, B.R.Ratna, and R.Shashidhar, Phys. Rev. E 57, 3059 (1998).
- [15] F. J. Bartoli, J. R. Lindle, S. R. Flom, R. Shashidhar, G. Rubin, J.V. Selinger, and B. R. Ratna, Phys. Rev. E 58, 5990 (1998).
- [16] J.V. Selinger, J.Xu, R.L.B. Selinger, B.R. Ratna, and R. Shashidhar, Phys. Rev. E 62, 666 (2000).
- [17] R.B.Meyer, private communication.
- [18] D. Shenoy, A. Lavarello, J. Naciri, and R. Shashidhar, Liq. Cryst. 28, 841 (2001).
- [19] J.Ruth, J.V. Selinger, and R. Shashidhar, Appl. Phys. Lett. 65, 1590 (1994).
- [20] D. Hermann, L. Kom itov, S. T. Lagerwall, G. Andersson, R. Shashidhar, J. V. Selinger, and F. Giesselmann, Ferroelectrics 181, 371 (1996).
- [21] K.A.Crandall, private communication.
- [22] J. Naciri, B. R. Ratna, S. Baral-Tosh, P. Keller, and R. Shashidhar, Macrom olecules 28, 5274 (1995).